
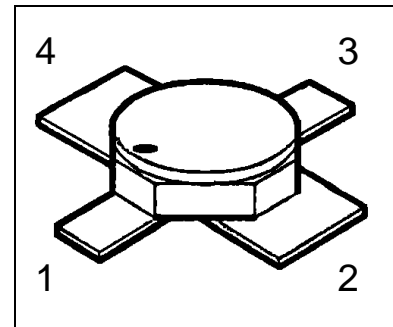


HiRel NPN Silicon RF Transistor

- **HiRel Discrete and Microwave Semiconductor**
- For Medium Power Amplifiers
- Compression Point $P_{-1dB} = 19dBm$ 1.8 GHz
Max. Available Gain $G_{ma} = 16dB$ at 1.8 GHz
- Hermetically sealed microwave package
- Transition Frequency $f_T = 20$ GHz
- **SIEGET[®] 25-Line**
Infineon Technologies Grounded Emitter Transistor-
25 GHz f_T -Line
-  **ESA Space Qualified**
ESA/SCC Detail Spec. No.: 5611/008
Type Variant No. 03



ESD: Electrostatic discharge sensitive device,
observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration				Package
			1	2	3	4	
BFY450 (ql)	-	see below	C	E	B	E	Micro-X

(ql) Quality Level: P: Professional Quality
 H: High Rel Quality
 S: Space Quality
 ES: ESA Space Quality

(see order instructions for ordering example)

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CEO}	4.5	V
Collector-base voltage	V_{CBO}	15	V
Emitter-base voltage	V_{EBO}	1.5	V
Collector current	I_C	100	mA
Base current	I_B	10	mA
Total power dissipation, $T_S \leq 110^\circ\text{C}$ ^{1), 2)}	P_{tot}	450	mW
Junction temperature	T_j	175	$^\circ\text{C}$
Operating temperature range	T_{op}	-65...+175	$^\circ\text{C}$
Storage temperature range	T_{stg}	-65...+175	$^\circ\text{C}$

Thermal Resistance

Junction-soldering point ²⁾	$R_{th JS}$	< 145	K/W
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Notes.:

1) At $T_S = +110^\circ\text{C}$. For $T_S > +110^\circ\text{C}$ derating is required.

2) T_S is measured on the collector lead at the soldering point to the pcb.

Electrical Characteristics

at $T_A = 25^\circ\text{C}$; unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-base cutoff current $V_{CB} = 5\text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Collector-emitter cutoff current ^{1.)} $V_{CE} = 4.5\text{ V}, I_B = 1.0\mu\text{A}$	I_{CEX}	-	-	200 (t.b.d.)	μA
Emitter-base cutoff current $V_{EB} = 1.5\text{ V}, I_C = 0$	I_{EBO}	-	-	50	μA
DC current gain $I_C = 20\text{ mA}, V_{CE} = 1\text{ V}$	h_{FE}	50	90	150	-

Notes:

1.) This Test assures $V(BR)_{CE0} > 4.5\text{V}$

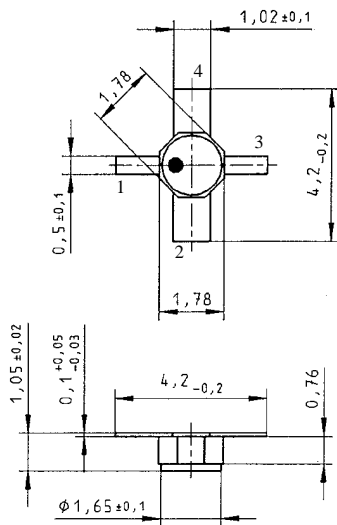
Electrical Characteristics (continued)

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 90\text{mA}$, $V_{CE} = 3\text{ V}$, $f = 1.0\text{ GHz}$ $I_C = 90\text{mA}$, $V_{CE} = 3\text{ V}$, $f = 2.0\text{ GHz}$	f_T	18 -	22 17	- -	GHz
Collector-base capacitance $V_{CB} = 2\text{ V}$, $V_{BE} = v_{be} = 0$, $f = 1\text{ MHz}$	C_{CB}	-	0.42	0.9	pF
Collector-emitter capacitance $V_{CE} = 2\text{ V}$, $V_{BE} = v_{be} = 0$, $f = 1\text{ MHz}$	C_{CE}	-	1.27	2.6	pF
Emitter-base capacitance $V_{EB} = 0.5\text{V}$, $V_{CB} = v_{cb} = 0$, $f = 1\text{ MHz}$	C_{EB}	-	2.0	3	pF
Noise Figure $I_C = 10\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{\text{sopt}}$	F	-	1.25	2.0	dB
Insertion power gain $I_C = 50\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 1.8\text{ GHz}$ $Z_S = Z_L = 50\ \Omega$	$ S_{21e} ^2$	8.0	12	-	dB
Power gain $I_C = 50\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 1.8\text{ GHz}$ $Z_S = Z_{\text{Sopt}}$, $Z_L = Z_{\text{Lopt}}$	$G_{ma}^{1.)}$	-	16.0	-	dB
1dB Compression point $I_C = 50\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 1.8\text{ GHz}$ $Z_S = Z_{\text{Sopt}}$, $Z_L = Z_{\text{Lopt}}$	$P_{-1\text{dB}}$	-	19	-	dBm

Notes.:

$$1) \quad G_{ma} = \left| \frac{S_{21}}{S_{12}} \right| (k - \sqrt{k^2 - 1}), \quad G_{ms} = \left| \frac{S_{21}}{S_{12}} \right|$$

Micro-X Package



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